Electronic Supplementary Information for

Sb@C coaxial nanotubes as superior long-life and high-rate anode for

sodium ion batteries

Zhiming Liu,^{a‡} Xin-Yao Yu,^{ab‡} Xiong Wen (David) Lou*^{bc} and Ungyu Paik*^a

^a Department of Energy Engineering, Hanyang University, 222 Wangsimni-ro, Seongdong-gu,
 Seoul, 04763, Korea E-mail: upaik@hanyang.ac.kr

- ^b State Key Laboratory of Silicon Materials, School of Materials Science and Engineering, Zhejiang University, Hangzhou, 310027, P. R. China Email: davidlou88@gmail.com
- ^c School of Chemical and Biomedical Engineering, Nanyang Technological University, 62
 Nanyang Drive, Singapore 637459, Singapore E-mail: xwlou@ntu.edu.sg

[‡] These authors contributed equally to this work.

Experimental Section

Synthesis of Sb_2S_3 nanorods: The Sb₂S₃ nanorods were synthesized through a simple hydrothermal method. In a typical synthesis, 4 mmol of SbCl₃, 8 mmol of L-cysteine, and 8 mmol of Na₂S 9H₂O were orderly dissolved in 80 mL of distilled water (DIW) under stirring for 3 h to form a homogeneous suspension. Afterwards, the above solution was transferred into a 100 mL Teflon-lined stainless steel autoclave and then kept at 180 °C for 12 h. After cooling down to room temperature naturally, the obtained dark-brown product was separated by centrifugation, washed with DIW and ethanol for several time before drying at 60 °C overnight under vacuum.

Synthesis of $Sb_2S_3@PDA$ core-shelled nanorods: 30 mg of Sb_2S_3 nanorods and 40 mg of dopamine hydrochloride were dispersed into 100 mL of Tris-buffer solution (10 mM) with

sonication for 10 minutes and then magnetic-stirring for 3 h. The resultant product was collected via centrifugation and washed with DIW and ethanol for three times, respectively, and dried at 60 \degree overnight under vacuum.

Synthesis of Sb@C coaxial nanotubes: Sb_2S_3 nanorods were annealed at 500 °C for 1 h in Ar with a heating rate of 3 °C min⁻¹. The as-prepared Sb_2S_3 @PDA core-shelled nanorods were annealed at 500 °C in Ar with a heating rate of 3 °C min⁻¹ for 2, 5, 20, and 40 min, respectively. After different annealing time, Sb_2S_3 @PDA core-shelled nanorods are transformed into Sb@C doble-walled nanotubes.

Materials characterization: Field-emission scanning electron microscope (FESEM; JEOL JSM07600F) and transmission electron microscope (TEM; JEOL JEM-2100F) were used to characterize the microscopic features of the samples. A Rigaku D/MAX RINT-2000 X-Ray Diffractometer with Cu K α radiation at a voltage of 40 kV and a current of 40 mA was used to collect the XRD patterns of the products. Thermogravimetric analysis (TGA) was performed with a temperature ramp of 10 °C min⁻¹ under air flow.

Electrochemical measurements: The battery tests were carried out in a half-cell configuration. The working electrode consists of active materials, conductivity agent (Carbon black, CB), and binder (Carboxymethylcellulose sodium, CMC-Na) with a weight ratio of 70:20:10. The mass loading of active materials was about 0.9 mg. The electrolyte was a solution of 1.0 M NaClO₄ in propylene carbonate with 5% fluoroethylene carbonate (FEC) additive. Sodium metal was used as both the counter electrode and reference electrode. The coin-type half cells were assembled in argon-filled glovebox and then tested in TOSCAT 3000 battery tester (TOSCAT 3000, Toyo Systems, Tokyo, Japan) with a voltage range between 0.01 and 2.0 V. Cyclic Voltammetry (CV) curves were tested using AUTOLAB potentiostat/galvanostat apparatus (AUT85698) with a scan rate of 0.1 mV s⁻¹.

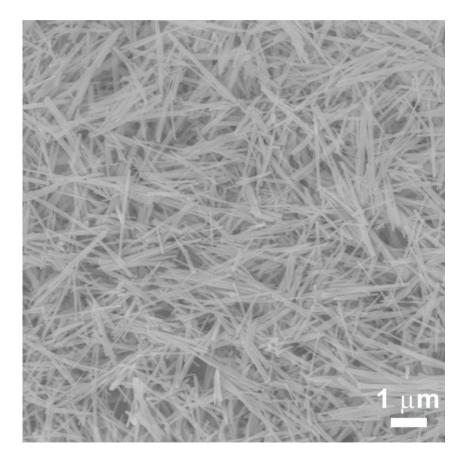


Fig. S1 FESEM image of Sb_2S_3 nanorods.

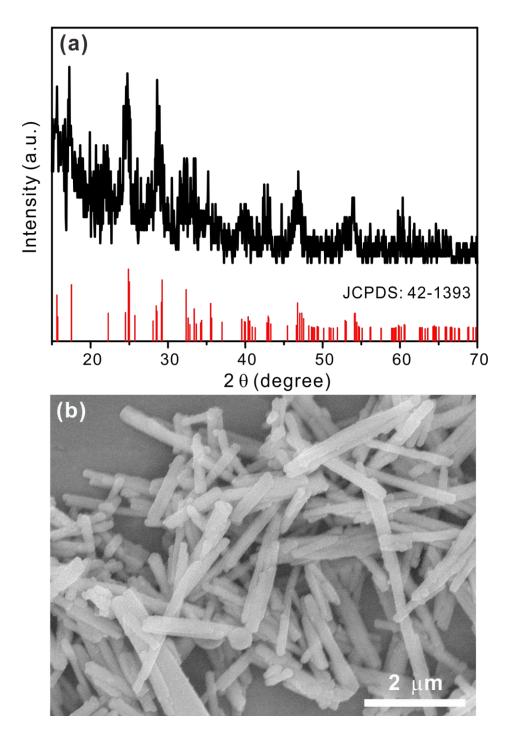


Fig. S2 XRD pattern and FESEM image of $Sb_2S_3@PDA$ core-shell nanorods.

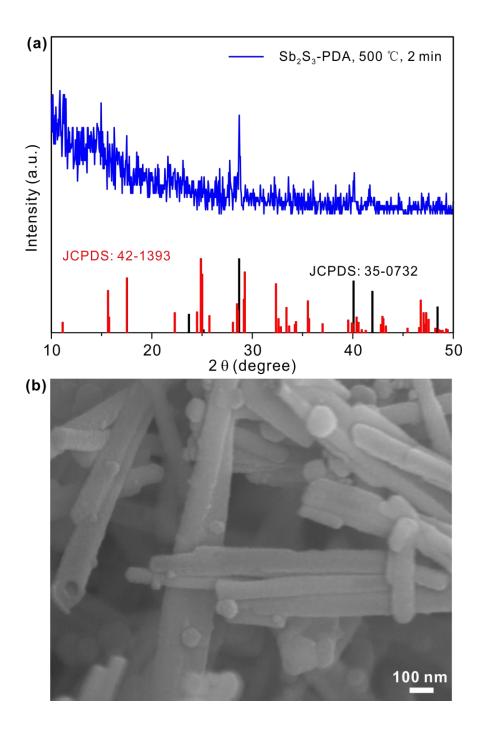


Fig. S3 XRD pattern (a) and FESEM image (b) of Sb₂S₃@PDA-2.

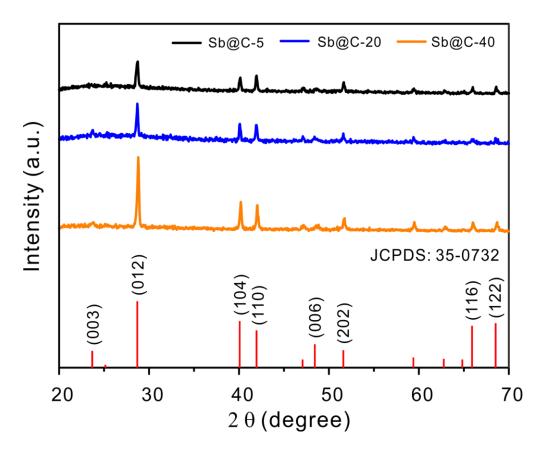


Fig. S4 XRD patterns of Sb@C-5, Sb@C-20, and Sb@C-40.

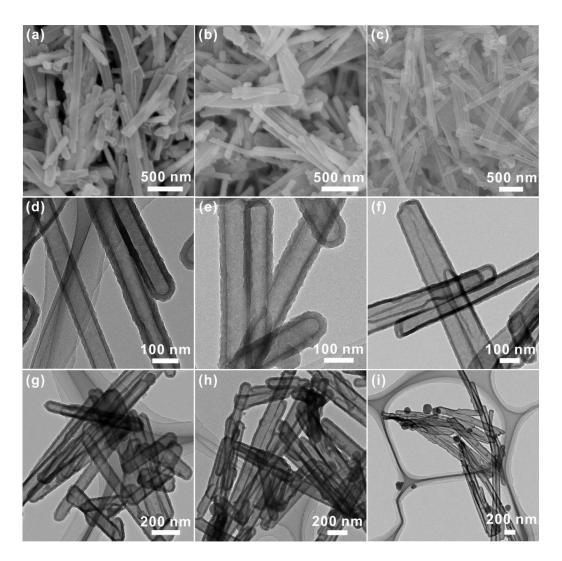


Fig. S5 FESEM (a, b, c) and TEM (c, e, f, g, h, i) images of Sb@C-5 (a, d, g), Sb@C-20 (b, e, h), and Sb@C-40 (c, f, i).

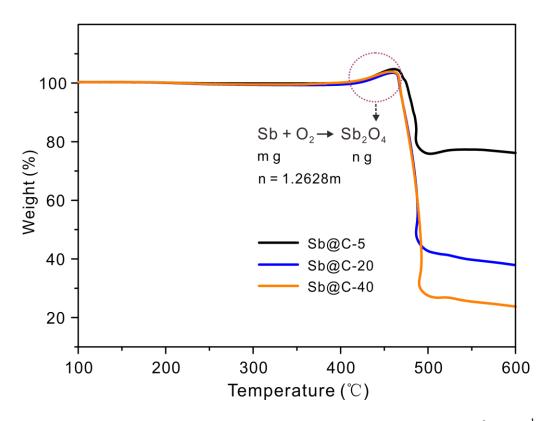


Fig. S6 TGA analysis of Sb@C coaxial nanotubes at a temperature ramp of 10 °C min⁻¹ in air.

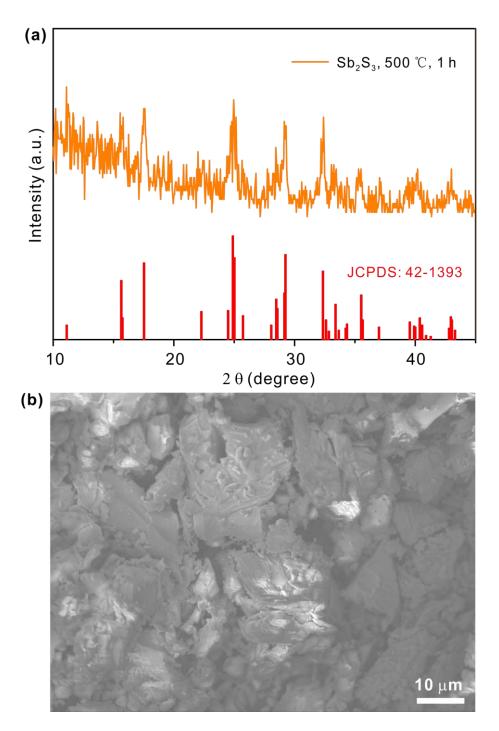


Fig. S7 XRD pattern and FESEM image of Sb_2S_3 nanorods after annealing at 500 °C for 1 h in Ar.

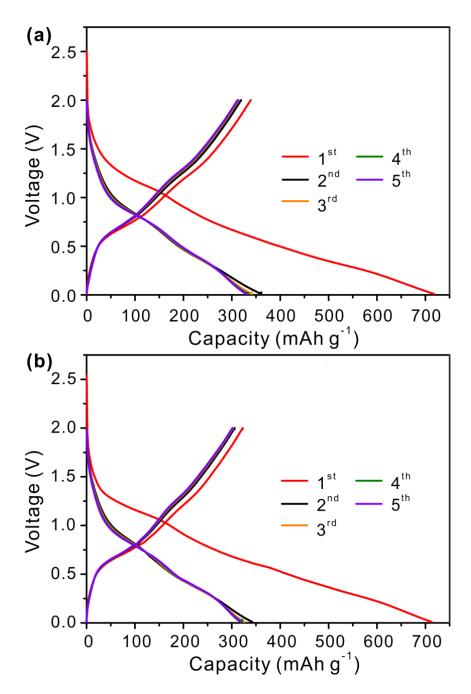


Fig. S8 Charge-discharge voltage profiles of Sb@C-20 (a) and Sb@C-40 (b) for the first five cycles at a current density of 100 mA g^{-1} .

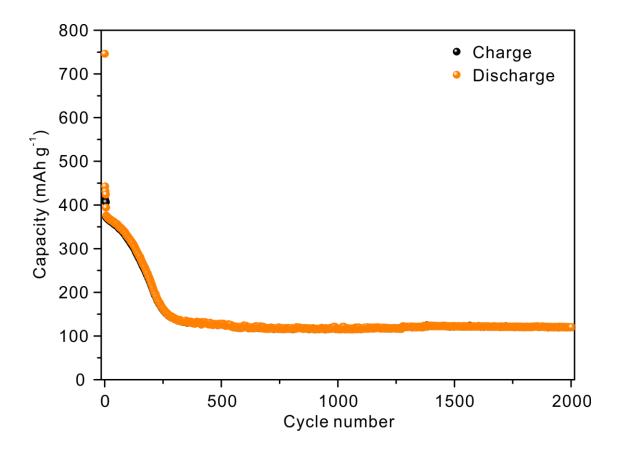


Fig. S9 Cycling performance of $Sb_2S_3@PDA-2$ at a current density of 1.0 A g⁻¹.

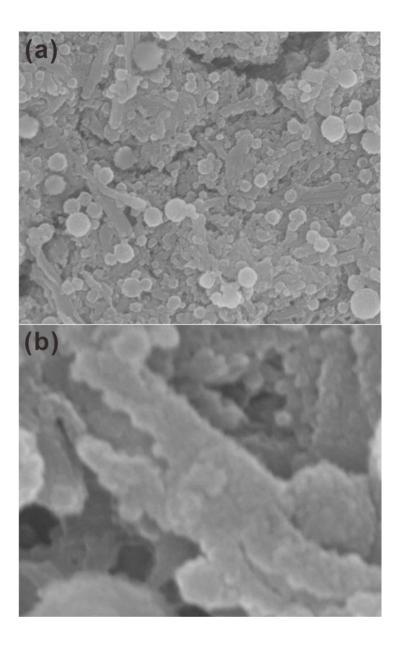


Fig. S10 FESEM images of Sb@C-5 after 2000 cycles at a current density of 1.0 A g^{-1} .

Cycling performance	Rate capability	Ref.
$305 \text{ mAh g}^{-1} \text{ after } 60 \text{ cycles at } 50 \text{ mA g}^{-1}$	$142 \text{ mAh g}^{-1} \text{ at } 10 \text{ A} \text{g}^{-1}$	[1]
350 mAh g^{-1} after 300 cycles at 100 mA g^{-1}	88 mAh g^{-1} at 6 A g^{-1}	[2]
385 mAh g^{-1} after 500 cycles at 100 mA g^{-1}	337 mAh g^{-1} at 3 A g ⁻¹	[3]
622.2 mAh g^{-1} after 50 cycles at 50 mA g^{-1}	315 mAh g^{-1} at 1.6 A g ⁻¹	[4]
574 mAh g^{-1} after 100 cycles at 660 mA g^{-1}	313 mAh g^{-1} at 3.2 A g ⁻¹	[5]
385 mAh g^{-1} after 500 cycles at 100 mA g^{-1}	270 mAh g^{-1} at 4 A g $^{-1}$	[6]
405 mAh g^{-1} after 200 cycles at 100 mA g^{-1}	210 mAh g^{-1} at 5 A g ⁻¹	[7]
380 mAh g^{-1} after 120 cycles at 200 mA g^{-1}	$\begin{array}{c} 225 \text{ mAh } \text{g}^{-1} \text{ at } 2 \text{ A} \\ \text{g}^{-1} \end{array}$	[8]
407 mAh g^{-1} after 240 cycles at 100 mA g^{-1}	460 mAh g^{-1} at 100 mA g^{-1}	
	350 mAh g^{-1} at 10 A g ⁻¹	Present work
230 mAh g^{-1} after 2000 cycles at 1 A g^{-1}	310 mAh g^{-1} at 20 A g ⁻¹	
	305 mAh g ⁻¹ after 60 cycles at 50 mA g ⁻¹ 350 mAh g ⁻¹ after 300 cycles at 100 mA g ⁻¹ 385 mAh g ⁻¹ after 500 cycles at 100 mA g ⁻¹ 622.2 mAh g ⁻¹ after 50 cycles at 50 mA g ⁻¹ 574 mAh g ⁻¹ after 100 cycles at 660 mA g ⁻¹ 385 mAh g ⁻¹ after 500 cycles at 100 mA g ⁻¹ 405 mAh g ⁻¹ after 200 cycles at 100 mA g ⁻¹ 380 mAh g ⁻¹ after 120 cycles at 200 mA g ⁻¹ 407 mAh g ⁻¹ after 240 cycles at 100 mA g ⁻¹	305 mAh g^{-1} after 60 cycles at 50 mA g^{-1} 142 mAh g^{-1} at 10 A g^{-1} 350 mAh g^{-1} after 300 cycles at 100 mA g^{-1} 88 mAh g^{-1} at 6 A g^{-1} 385 mAh g^{-1} after 500 cycles at 100 mA g^{-1} 337 mAh g^{-1} at 3 A g^{-1} 622.2 mAh g^{-1} after 50 cycles at 50 mA g^{-1} 315 mAh g^{-1} at 1.6 A g^{-1} 574 mAh g^{-1} after 100 cycles at 660 mA g^{-1} 313 mAh g^{-1} at 3.2 A g^{-1} 385 mAh g^{-1} after 200 cycles at 100 mA g^{-1} 270 mAh g^{-1} at 4 A g^{-1} 380 mAh g^{-1} after 120 cycles at 200 mA g^{-1} 210 mAh g^{-1} at 2 A g^{-1} 407 mAh g^{-1} after 240 cycles at 100 mA g^{-1} 350 mAh g^{-1} at 10 A g^{-1} 407 mAh g^{-1} after 240 cycles at 100 mA g^{-1} 310 mAh g^{-1} at 20 A

Table S1. Comparison of some representative Sb-based anode materials for SIBs.

References

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